

**1. Material** Substrate GaAs (N Type)  
 Epitaxial Layer GaAs (P/N Type)

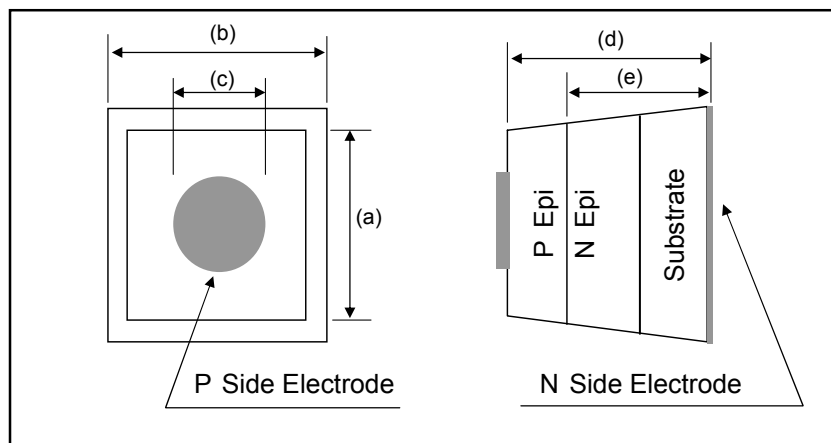
**2. Electrode** N(Cathode) Side Gold Alloy  
 P(Anode) Side Aluminum Alloy

**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_F$		1.3	1.45	V	IF=20mA
Reverse Voltage	$V_R$	8			V	IR=10uA
Power	$P_O$	A	1.14		mW	IF=20mA
		B	1.22			
		C	1.30			
		D	1.38			
		E	1.46			
		F	1.54			
Wavelength	$\lambda_P$		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : LED Chip is mounted on TO-18 gold header without resin coating

**4. Mechanical Data** (a) Emission Area ----- 9mil x 9mil  
 (b) Bottom Area ----- 10mil x 10mil  
 (c) Bonding Pad ----- 130um  
 (d) Chip Thickness ----- 10mil  
 (e) Junction Height ----- 6.5mil



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